

IRFP4410ZPbF

HEXFET® Power MOSFET

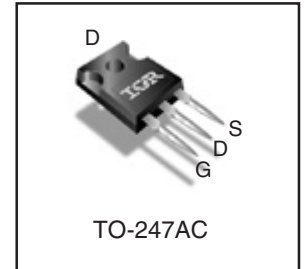
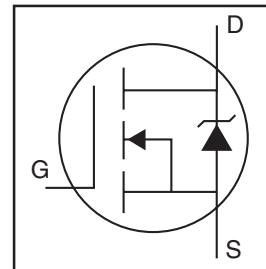
Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free

V_{DSS}	100V
$R_{DS(on)}$ typ.	7.2mΩ
max.	9.0mΩ
I_D (Silicon Limited)	97A



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	97	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	69	
I_{DM}	Pulsed Drain Current ①	390	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	230	W
	Linear Derating Factor	1.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ③	16	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Avalanche Characteristics

E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	242	mJ
I_{AR}	Avalanche Current ①	See Fig. 14, 15, 22a, 22b,	A
E_{AR}	Repetitive Avalanche Energy ④		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	---	0.65	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient ⑧	---	40	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.12	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 5mA$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	7.2	9.0	m Ω	$V_{GS} = 10V, I_D = 58A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 150\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
R_G	Internal Gate Resistance	—	0.70	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

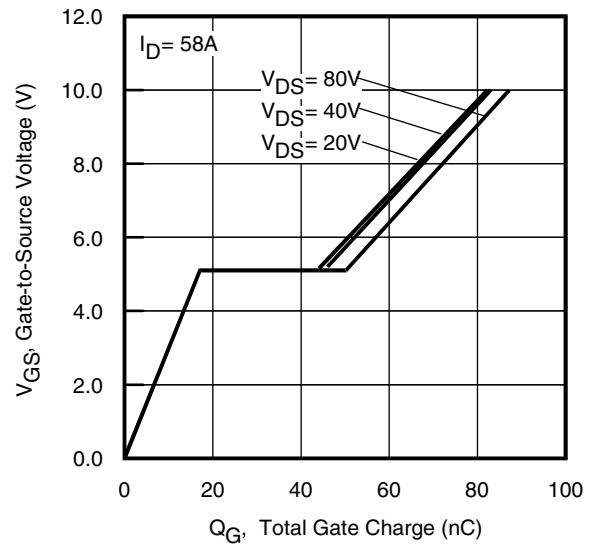
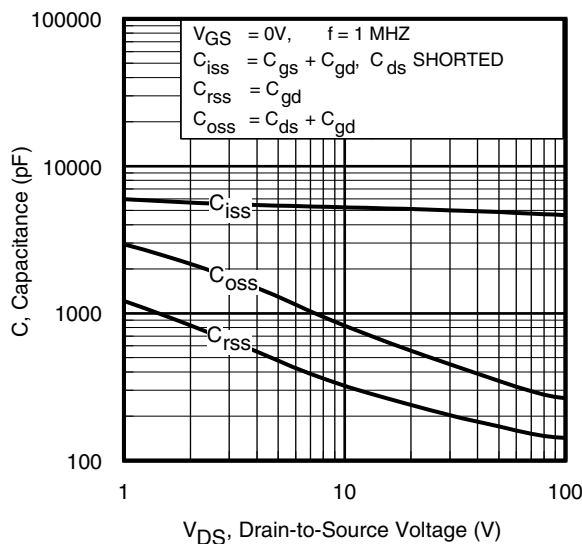
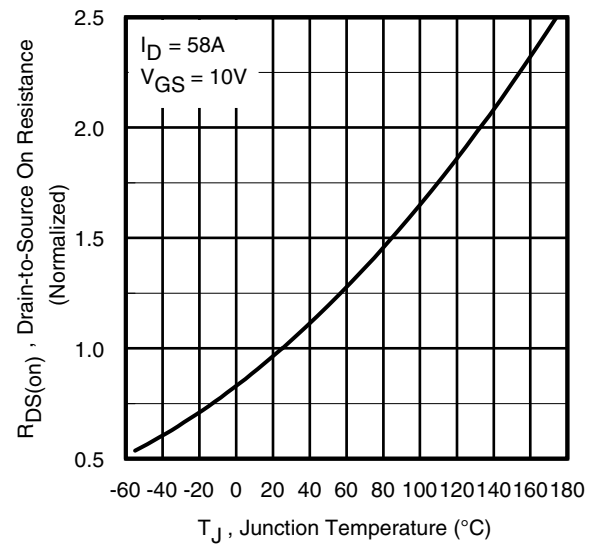
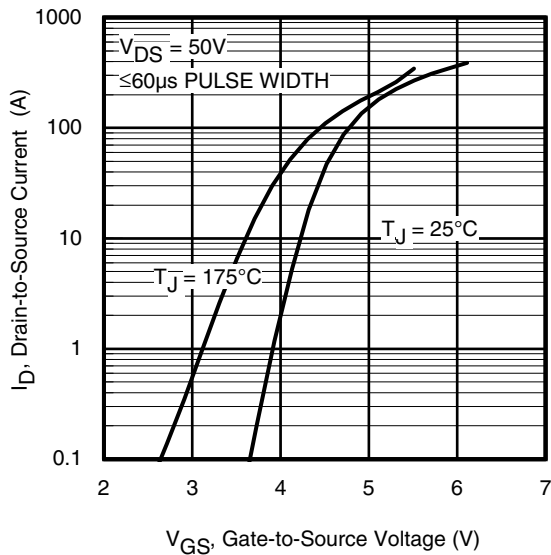
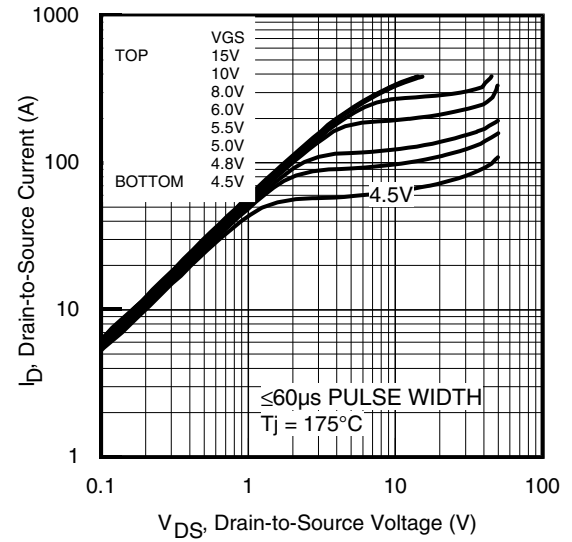
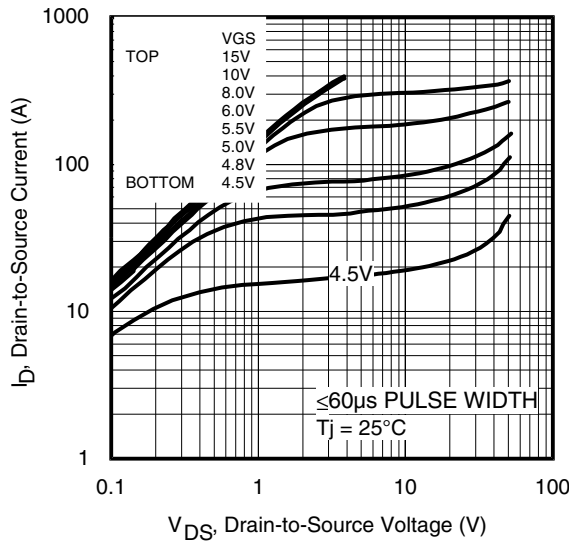
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	140	—	—	S	$V_{DS} = 10V, I_D = 58A$
Q_g	Total Gate Charge	—	83	120	nC	$I_D = 58A$
Q_{gs}	Gate-to-Source Charge	—	19	—		$V_{DS} = 50V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	27	—		$V_{GS} = 10V$ ④
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	56	—		$I_D = 58A, V_{DS} = 0V, V_{GS} = 10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 65V$
t_r	Rise Time	—	52	—		$I_D = 58A$
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		$R_G = 2.7\Omega$
t_f	Fall Time	—	57	—		$V_{GS} = 10V$ ④
C_{iss}	Input Capacitance	—	4820	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	340	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	170	—		$f = 1.0MHz$, See Fig.5
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related) ⑥	—	420	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑦, See Fig.11
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related) ⑤	—	690	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑧

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	97	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	390	A	
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 58A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	38	57	ns	$T_J = 25^\circ\text{C}$ $V_R = 85V,$
		—	46	69		$T_J = 125^\circ\text{C}$ $I_F = 58A$
Q_{rr}	Reverse Recovery Charge	—	53	80	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ④
		—	82	120		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	2.5	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.143mH$
 $R_G = 25\Omega, I_{AS} = 58A, V_{GS} = 10V$. Part not recommended for use above this value.
- ③ $I_{SD} \leq 58A, di/dt \leq 610A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧ R_θ is measured at T_J approximately 90°C .



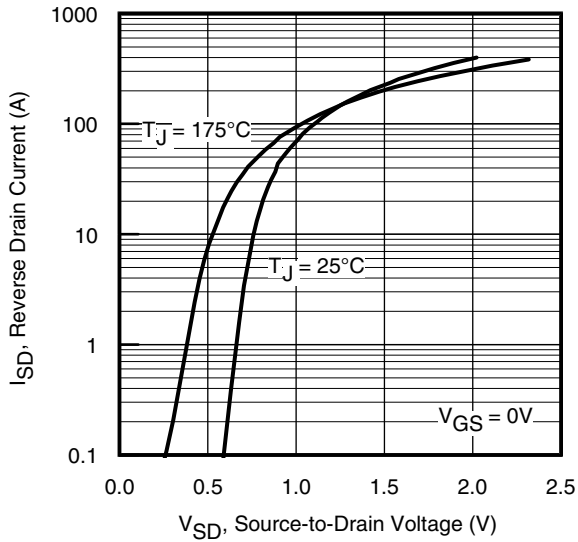


Fig 7. Typical Source-Drain Diode Forward Voltage

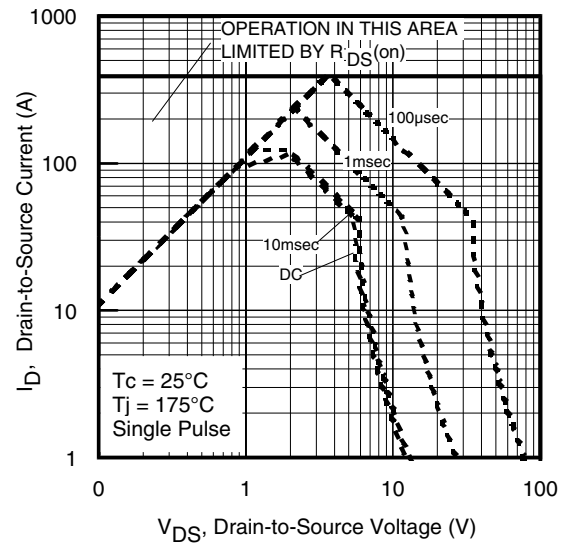


Fig 8. Maximum Safe Operating Area

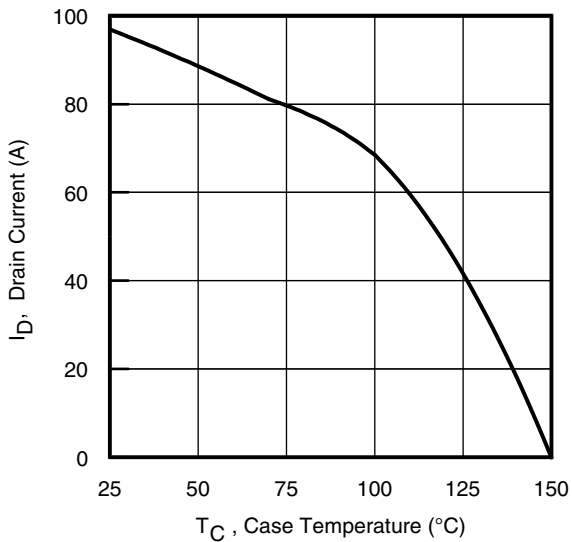


Fig 9. Maximum Drain Current vs. Case Temperature

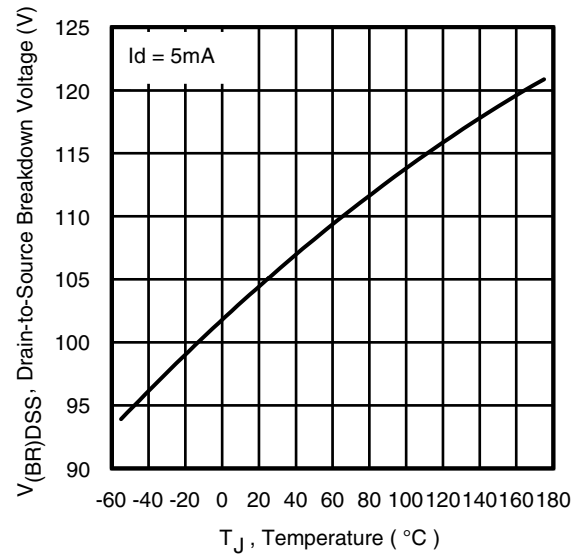


Fig 10. Drain-to-Source Breakdown Voltage

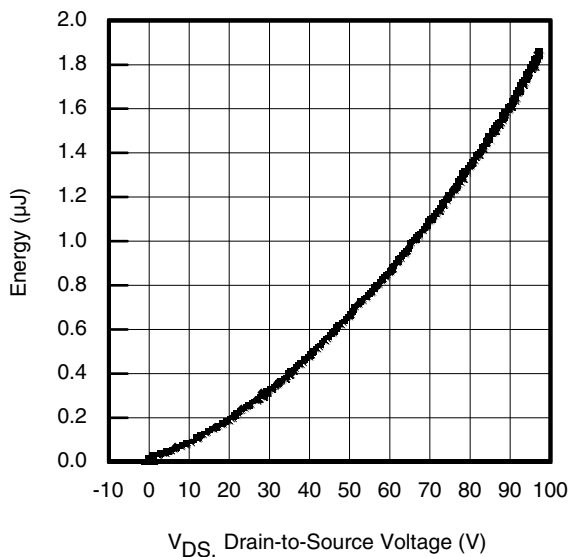


Fig 11. Typical C_{OSS} Stored Energy

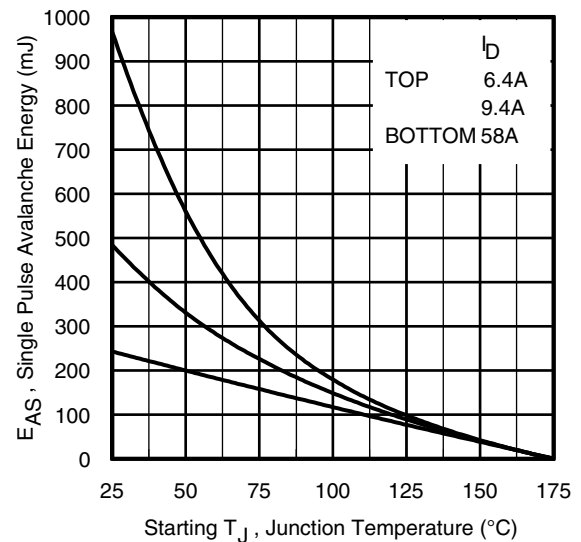


Fig 12. Maximum Avalanche Energy vs. Drain Current

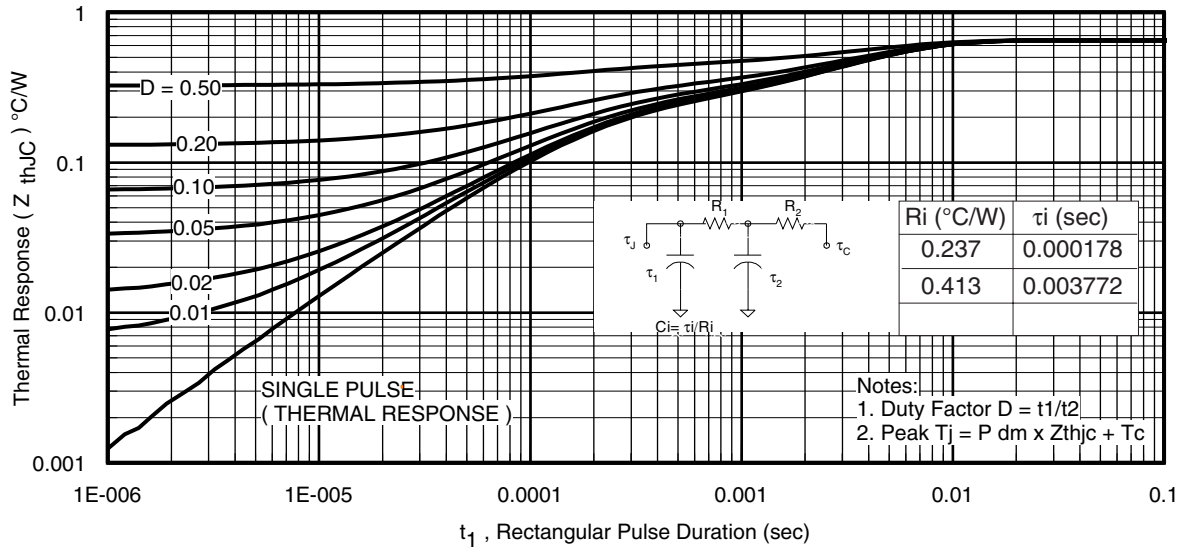


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

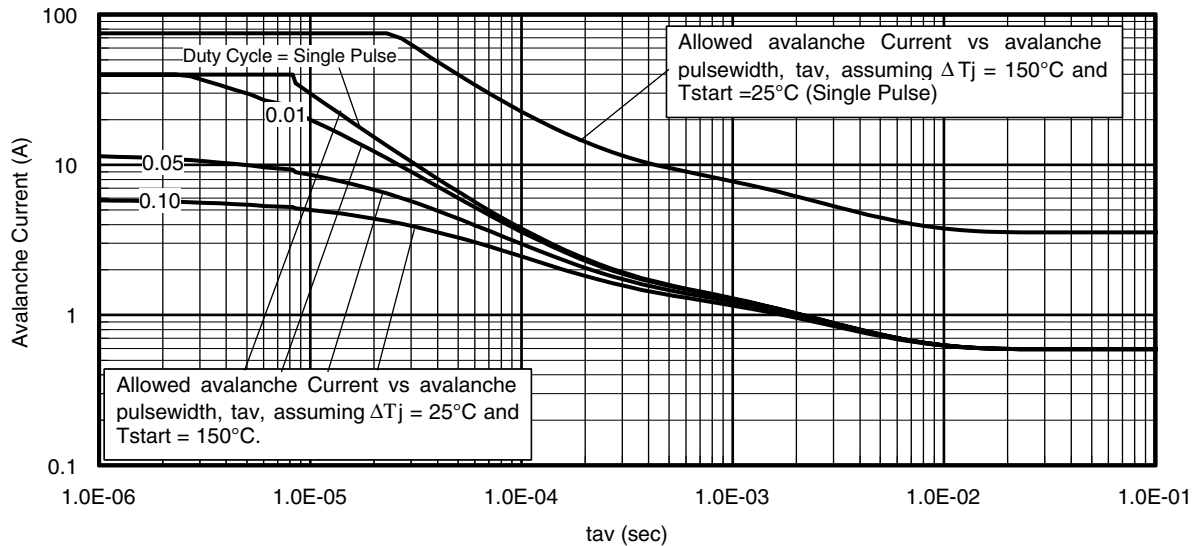


Fig 14. Typical Avalanche Current vs. Pulsewidth

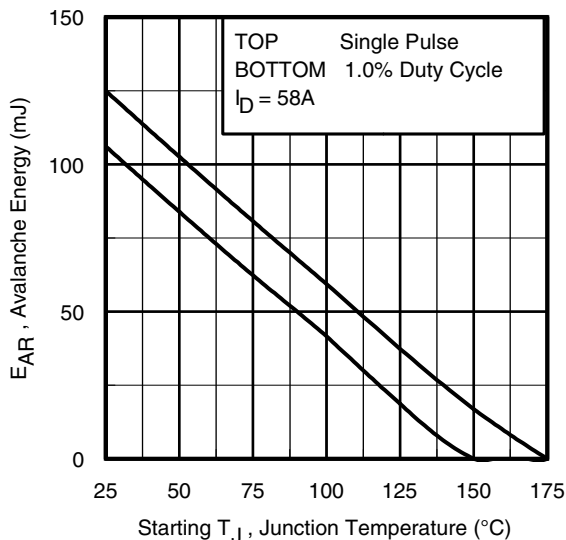


Fig 15. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

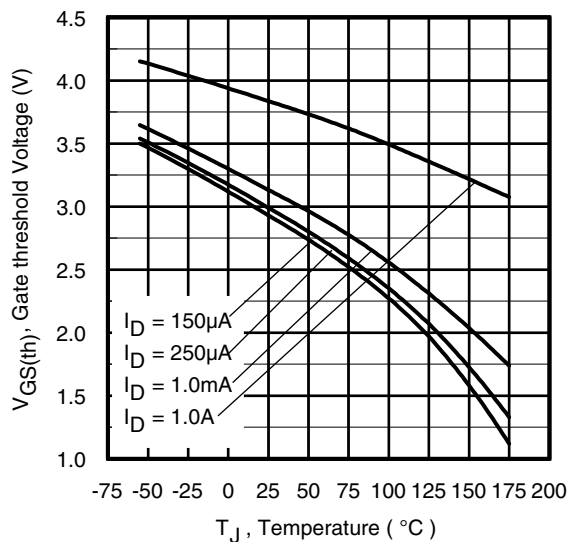


Fig 16. Threshold Voltage vs. Temperature

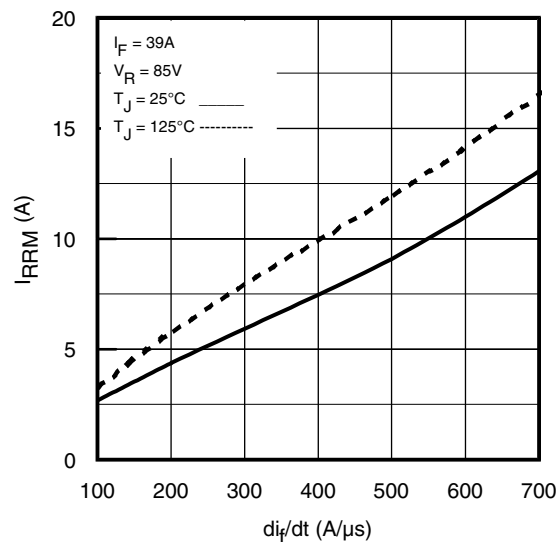


Fig. 17 - Typical Recovery Current vs. di/dt

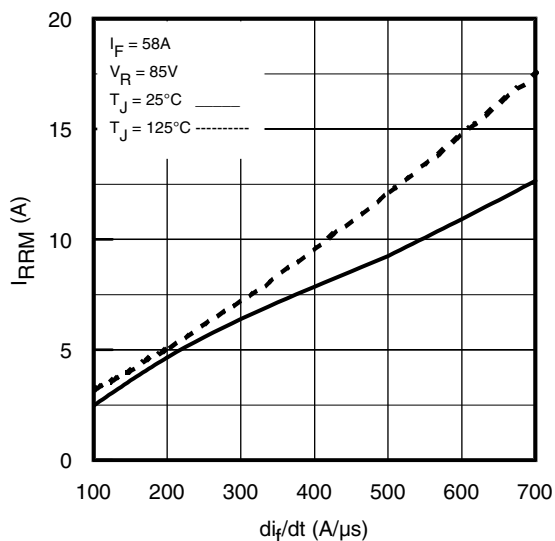


Fig. 18 - Typical Recovery Current vs. di/dt

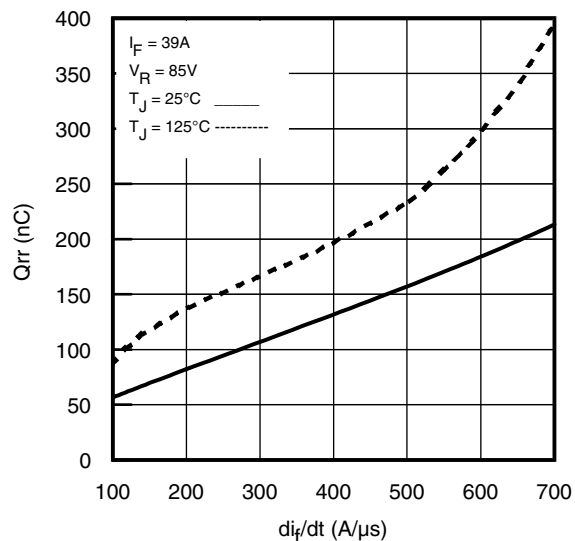


Fig. 19 - Typical Stored Charge vs. di/dt

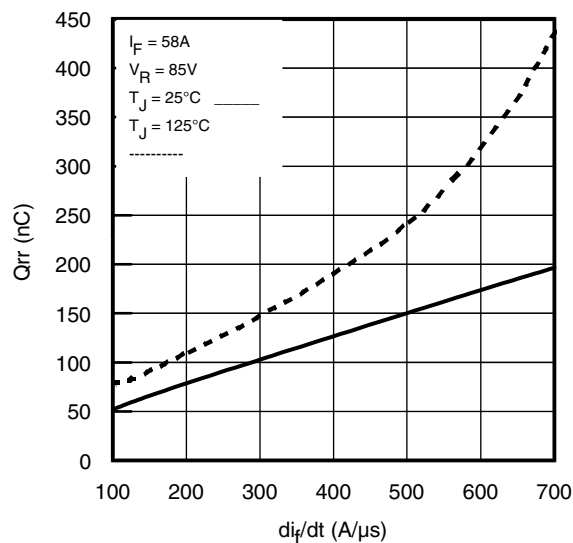


Fig. 20 - Typical Stored Charge vs. di/dt



Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

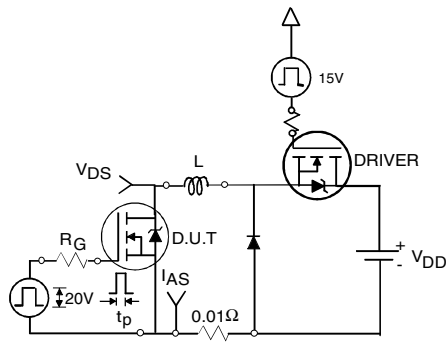


Fig 22a. Unclamped Inductive Test Circuit

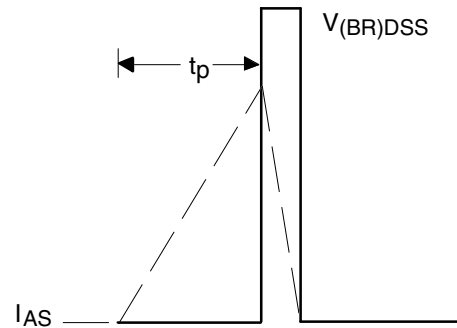


Fig 22b. Unclamped Inductive Waveforms

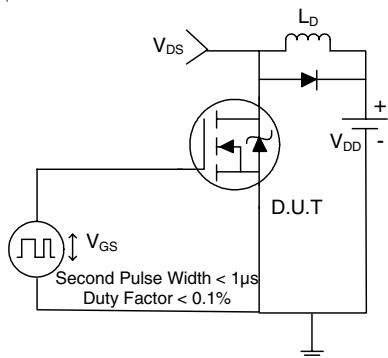


Fig 23a. Switching Time Test Circuit

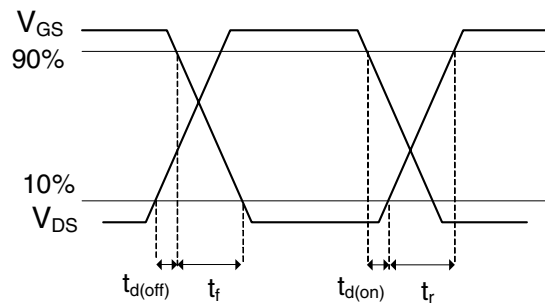


Fig 23b. Switching Time Waveforms

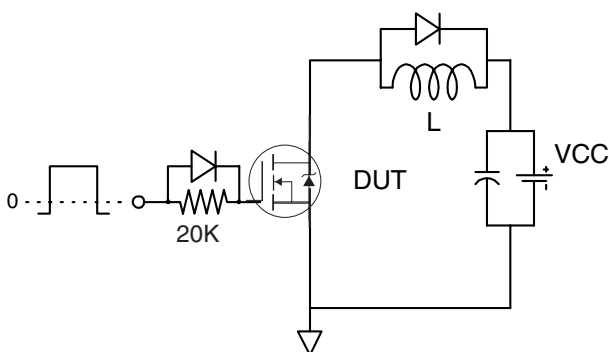


Fig 24a. Gate Charge Test Circuit

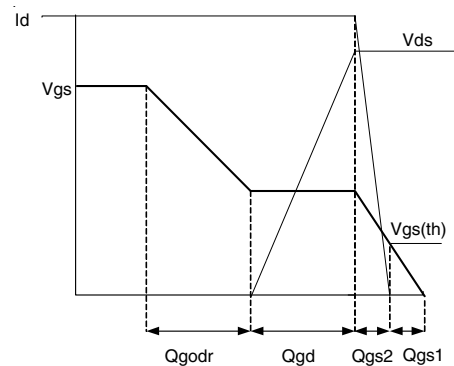
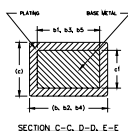
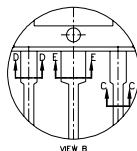
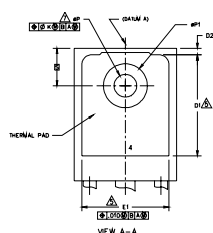


Fig 24b. Gate Charge Waveform

TO-247AC Package Outline

International
IOR Rectifier



SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
ek	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
lp	.140	.144	3.56	3.66	
oP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

Diagram illustrating the identification marks on the IRFPE30 MOSFET package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo.
- PART NUMBER**: Points to the text IRFPE30.
- DATE CODE**: Points to the text 135H.
- YEAR 1 = 2001**: Points to the first digit of the date code (1).
- WEEK 35**: Points to the second digit of the date code (5).
- LINE H**: Points to the third digit of the date code (H).
- ASSEMBLY LOT CODE**: Points to the text 56.

International
IOR Rectifier

8

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Infineon:](#)

[IRFP4410ZPBF](#)